



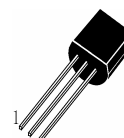
APPLICATIONS

FM RF amp , mixer , osc , converter , and IF amplifier.

ABSOLUTE MAXIMUM RATINGS ($T_a=25$)

T_{stg}	Storage Temperature.....	-55~150
T_j	Junction Temperature.....	150
P_C	Collector Dissipation.....	250mW
V_{CBO}	Collector-Base Voltage.....	30V
V_{CEO}	Collector-Emitter Voltage.....	20V
V_{EBO}	Emitter-Base Voltage.....	5V
I_C	Collector Current.....	30mA

TO-92



- 1—Emitter , E
- 2—Collector ,C
- 3—Base , B

ELECTRICAL CHARACTERISTICS ($T_a=25$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	30			V	$I_C=100\mu A$, $I_E=0$
BV_{CEO}	Collector-Emitter Breakdown Voltage	20			V	$I_C=5mA$, $I_B=0$
BV_{EBO}	Emitter-Base Breakdown Voltage	5			V	$I_E=100\mu A$, $I_C=0$
I_{CBO}	Collector Cut-off Current			1.0	μA	$V_{CB}=10V$, $I_E=0$
I_{EBO}	Emitter Cut-off Current			1.0	μA	$V_{EB}=4V$, $I_C=0$
h_{FE}	DC Current Gain	40	80	320		$V_{CE}=6V$, $I_C=1mA$
f_r	Current Gain-Bandwidth Product	170	300		MHz	$V_{CE}=6V$, $I_C=1mA$
NF	Noise Figure		4.0		dB	$V_{CE}=6V$, $I_C=1mA$, $f=100MHz$
t_{ON}	Turn-On Time		30		ns	$V_{IN}=+12V$, $V_{BB}=-3V$, appointed circuit
t_{OFF}	Turn-Off Time		30		ns	$V_{IN}=-12V$, $V_{BB}=+3V$, appointed circuit

h_{FE} Classification

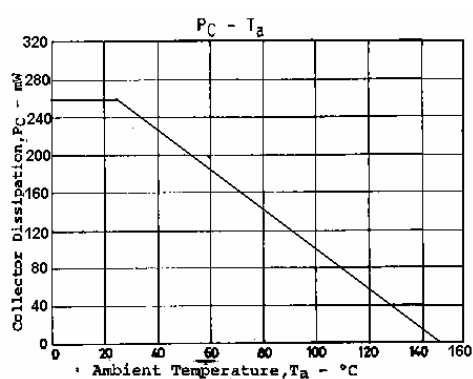
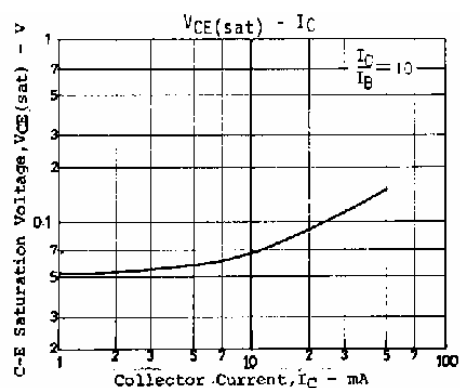
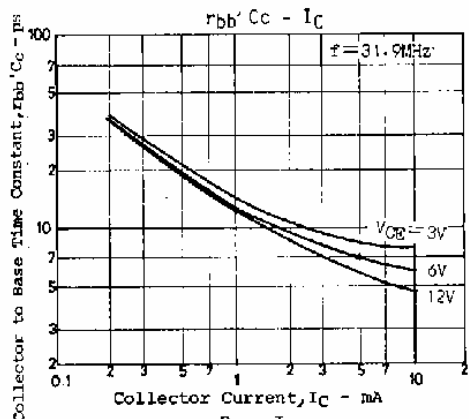
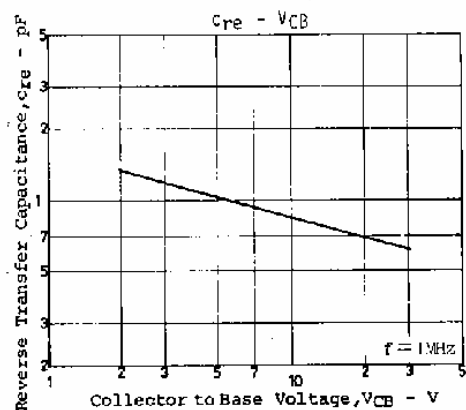
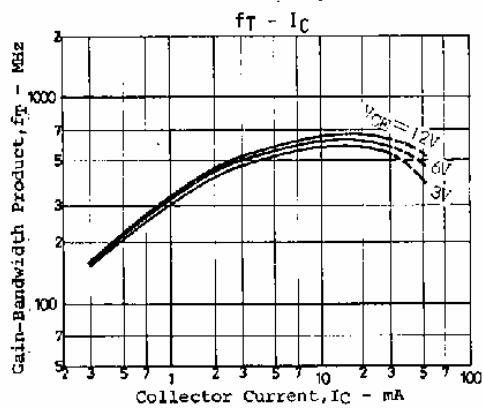
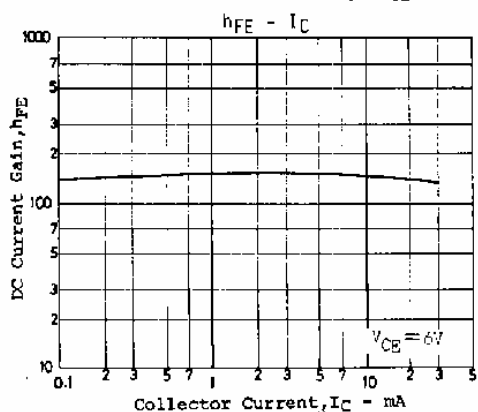
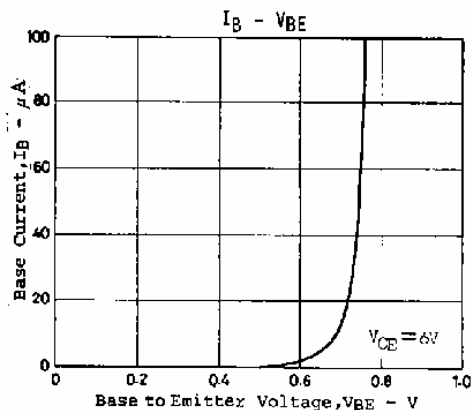
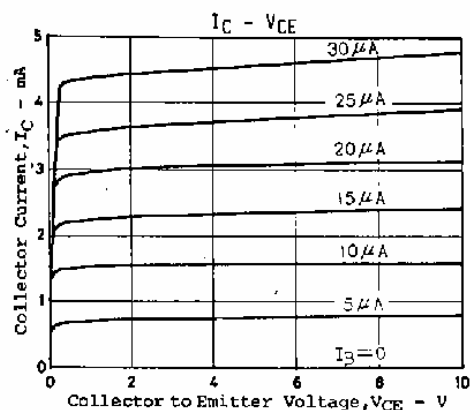
C	D	E	F
40—80	60--120	100--200	160--320



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NPN SILICON TRANSISTOR

H930

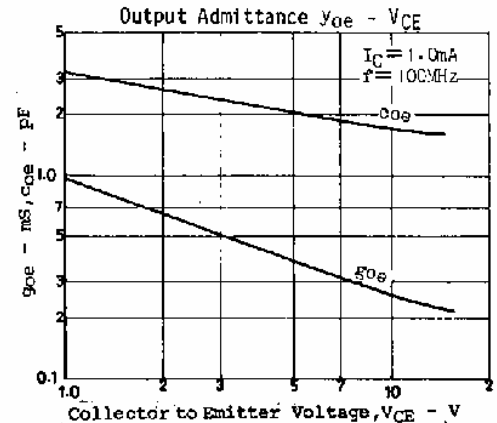
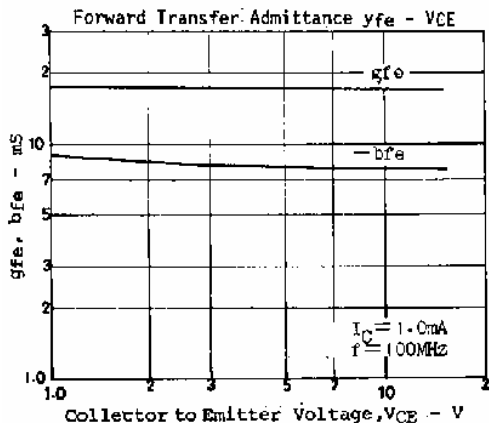
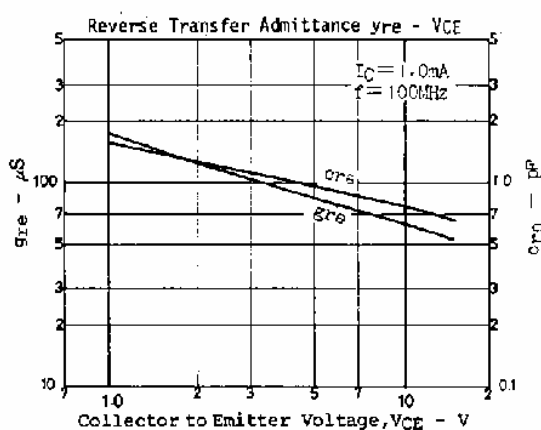
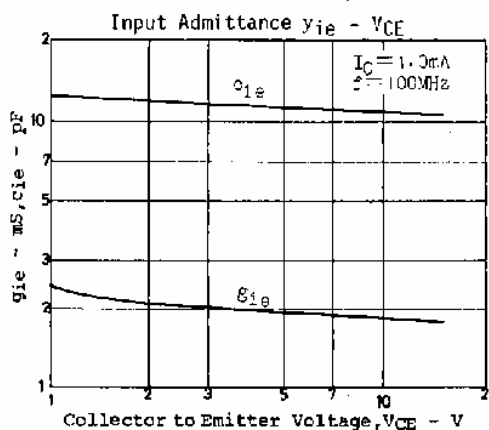
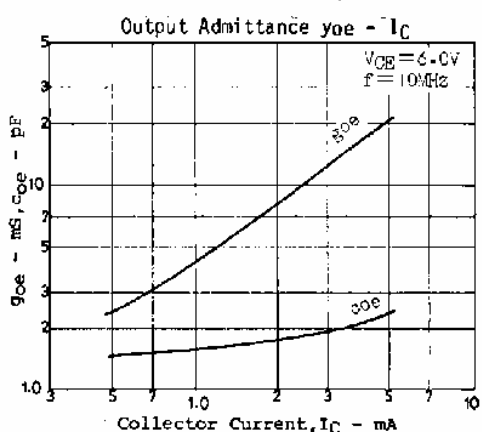
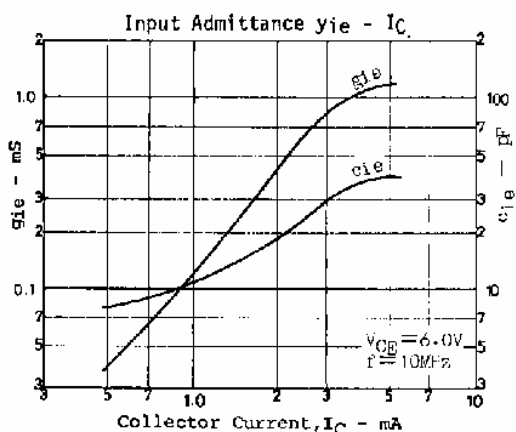
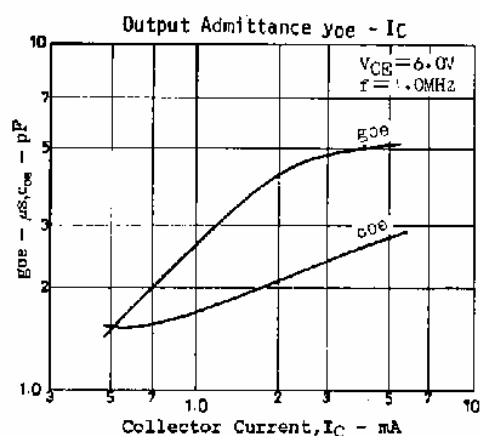
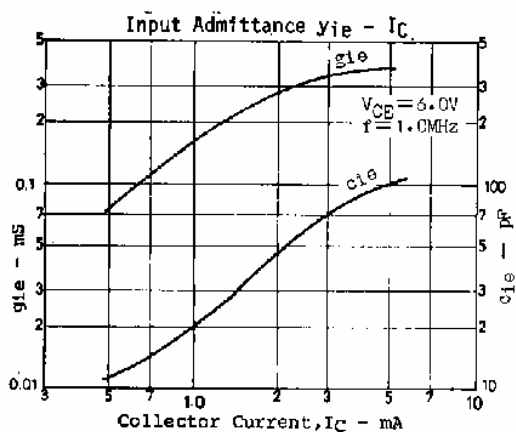




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